

ESE 568: Mixed Signal Design and Modeling

Lec 21: November 20, 2019
FOM, Performance Limits

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ADC Figures of Merit

- Objective
 - Want to compare performance of different ADCs
- Can use FOM to combine several performance metrics into one single number
- What are reasonable FOMs for ADCs?
- How can we use and interpret them?
- Trends?

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ADC Figures of Merit

$$FOM_1 = f_s \cdot 2^{ENOB}$$

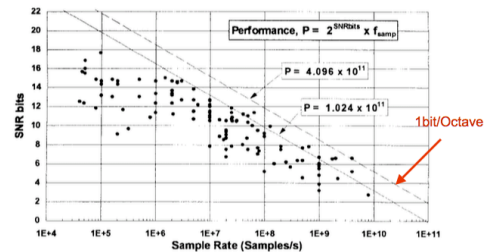
[R. H. Walden, "Analog-to-digital converter survey and analysis," *IEEE Journal on Selected Areas in Communications*, April 1999]

- This FOM suggests that adding a bit to an ADC is just as hard as doubling its bandwidth
- Is this a good assumption?

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Survey Data



[Walden, "Analog-to-digital converter survey and analysis," *IEEE J. Selected Areas Comm.*, April 1999]

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ADC Figures of Merit

$$FOM_2 = \frac{f_s \cdot 2^{ENOB}}{\text{Power}}$$

[R. H. Walden, "Analog-to-digital converter survey and analysis," *IEEE Journal on Selected Areas in Communications*, April 1999]

- Sometimes inverse of this metric is used
- In typical circuits power \sim speed
 - FOM2 captures this tradeoff correctly
- How about power vs. ENOB?
 - One additional bit = 2x in power?

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ADC Figures of Merit

- In a circuit that is limited by thermal noise, each additional bit in resolution means...
 - 6dB SNR \rightarrow 4x less noise power \rightarrow 4x bigger C
 - Power \sim Gm \sim C increases 4x

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ADC Figures of Merit

- In a circuit that is limited by thermal noise, each additional bit in resolution means...
 - 6dB SNR → 4x less noise power → 4x bigger C
 - Power ~ Gm ~ C increases 4x
- Even worse: Flash ADC
 - Extra bit means 2x number of comparators
 - Each of them needs double precision
 - Transistor area 4x, Current 4x to maintain current density
 - Net result: Power increases 8x

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ADC Figures of Merit

- FOM₂ is inappropriate for comparing ADCs that are limited by matching or thermal noise
 - Still the most widely used FOM in publications...
- "Tends to work" because not all power in an ADC is noise limited
 - E.g. Digital power, biasing circuits, etc.
- To better capture the case of noise limited circuits, one could use $2^{2 \cdot \text{ENOB}}$ in the numerator of FOM₂...

$$FOM_2 = \frac{f_s \cdot 2^{\text{ENOB} \times 2}}{\text{Power}}$$

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ADC Figures of Merit

$$FOM_3 = \frac{\text{Power}}{\text{Conversion Bandwidth}}$$

- Compare only power of ADCs with approximately same SNR or SNDR (ENOB)
- Useful numbers (~state-of-the-art):
 - 10b (~9ENOB) ADCs: 1...2mW/MHz
 - 12b (~11 ENOB) ADCs: 6...8 mW/MHz

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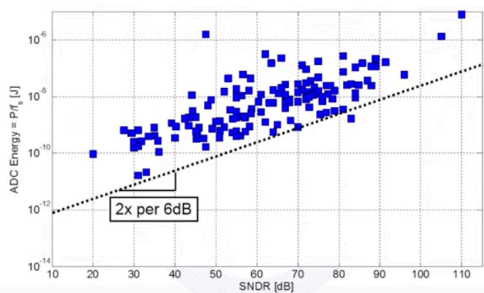
Which FOM?

- Different limiting mechanisms
 - Matching: Power grows 8x per added bit
 - Thermal Noise: Power grows 4x per added bit
 - Process CV²: Power grows 2x per added bit

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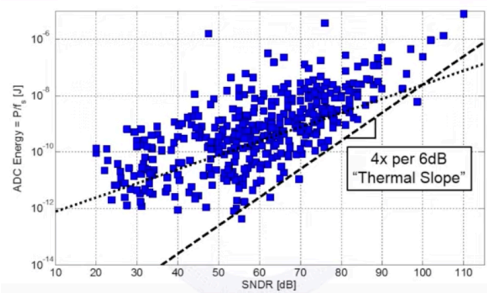
Survey Data 1997-2004



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Survey Data 1997-2014



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Popular FOM

- Walden FOM:

- 2x per bit

$$FOM_W = \frac{P}{f_s \cdot 2^{ENOB}}$$

- Schreier FOM

- 4x per bit
- Ignores distortion

$$FOM_{S,DR} = DR + 10 \log \left(\frac{BW}{P} \right)$$

- Schreier FOM

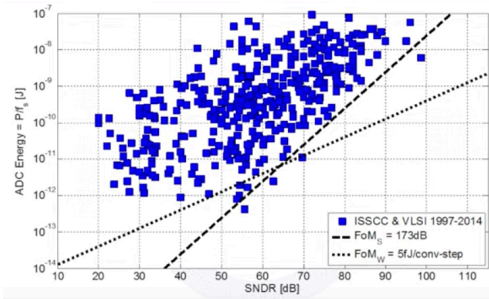
- 4x per bit
- Includes distortion

$$FOM_S = SNDR + 10 \log \left(\frac{f_i/2}{P} \right)$$

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Survey Data 1997-2014

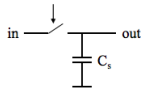


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Fundamental Power Limits

- Sampling Power



Noise voltage generated: $v_{as}^2 = \frac{kT}{C_s}$

Maximum sine voltage with supply voltage V_{FS} :

$$v_s^2 = \frac{V_{FS}^2}{8} \quad \text{gives dynamic range: } SNR = \frac{v_s^2}{v_{as}^2} = \frac{V_{FS}^2 C_s}{8kT}$$

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Fundamental Limits

- Fundamental power limit for a class-B amplifier driving a single capacitor [Vittoz, ISCAS 1990]

$$P = 8 \cdot f_{sig} \cdot C V_{sig}^2 \quad V_{sig}^2 = \frac{k_B T}{C} \quad SNR = \frac{0.5 \times V_{sig}^2}{V_n^2}$$

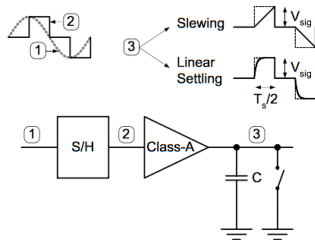
$$\therefore P = 8k_B T \cdot SNR \cdot f_{sig}$$

- Class-A power limit is π times higher

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Switched Cap Circuits



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Case 1: 100% Slewing

$$I_{bias} = C \cdot \frac{dV}{dt} = C \cdot \frac{V_{sig}}{T_s/2} = 4 \cdot C \cdot V_{sig} \cdot f_{sig}$$

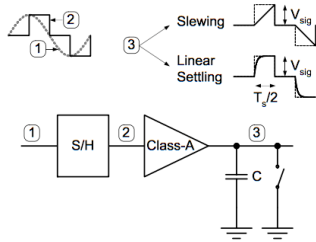
$$P = 2 \cdot V_{sig} \cdot I_{bias} \quad SNR = \frac{0.5 \times V_{sig}^2}{k_B T / C}$$

$$\therefore P = 16k_B T \cdot SNR \cdot f_{sig}$$

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Switched Cap Circuits



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Case 2: 100% Linear Settling

$$I_{bias} = C \cdot \left. \frac{dV}{dt} \right|_{max} = C \cdot \frac{d}{dt} \left[V_{sig} (1 - e^{-t/\tau}) \right] = 4 \cdot C \cdot \frac{V_{sig}}{\tau}$$

$$\text{Number of settling time constants: } N = \frac{T_s/2}{\tau}$$

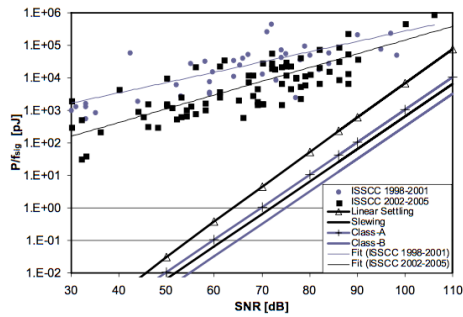
$$\therefore P = 16 \cdot N \cdot k_B T \cdot SNR \cdot f_{sig}$$

- Much worse
 - E.g. N=6.9 for settling to 0.1% precision

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Reality Check



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Discussion

- Orders of magnitude away from limits
- Slope of limit lines is much steeper than fit to experimental data
- What contributes to these large gaps?
 - Must keep in mind that ADCs are not just a single capacitor circuit...

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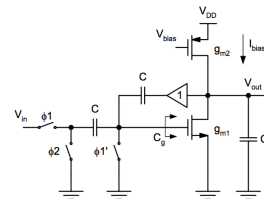
Design Space Partitioning

- High SNR
 - Complexity ~1 (e.g. first integrator in sigma-delta ADC)
 - Limited by thermal noise
- Medium SNR
 - Complexity ~Bits (e.g. pipelined ADC)
 - Partly limited by thermal noise
- Low SNR
 - Complexity ~2Bits (e.g. flash ADC)
 - Limited by matching, quantization noise

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High SNR: SC-Stage



- Considerations
 - Noise is multiple of $k_B T / C$ (n_2)
 - Swing is only a fraction of V_{DD} (α)
 - Feedback factor (β)
 - g_m / I_D is upper bounded if slewing must be avoided

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High SNR: SC-Stage

To avoid slewing: $\frac{g_{m1}}{I_{bias}} \leq \frac{1}{\beta \cdot V_{sig}}$

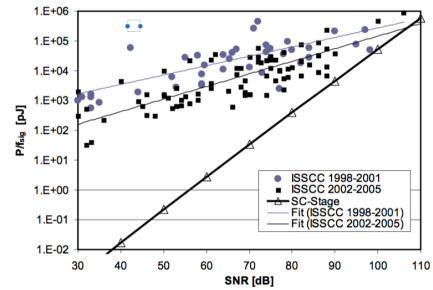
$$\therefore P = 16 \cdot N \cdot n_f \cdot \frac{1}{\alpha} \cdot k_B T \cdot SNR \cdot f_{sig} \cdot \max \left(1, \frac{I}{I_{bias} \cdot \beta \cdot V_{sig}} \right)$$

- Graph on following slide shows result assuming
 - $n_f=5$, $\alpha=2/3$, $\beta=0.5$, onset of slewing

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High SNR: SC-Stage



- Very close to experimental data at high SNR!

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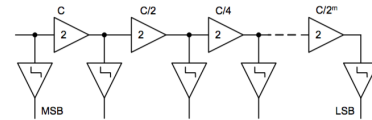
Medium SNR

- Pipeline ADC using SC stages
 - Partially limited by thermal noise

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Medium SNR: Pipeline ADC

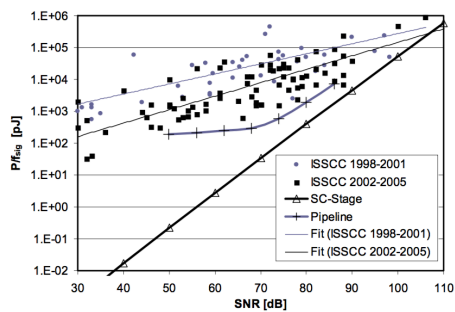


- Theoretical near optimum power scaling
 - Scale capacitance by gain of preceding stage
 - Stage 1 consumes half of total power
 - Adding one bit means power goes up 4x
- Caveat
 - Usually impractical to scale capacitors down to $C/2^m$
 - State-of-art: 10bits $\sim 2\text{mW/MHz}$, 12bits $\sim 8\text{mW/MHz}$

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Medium SNR: Results



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Low SNR

- Power of matching limited class-B circuit [Kinetz, CICC 1996]

$$P = 24 \cdot C_{ox} \cdot A_T^2 \cdot f_{sig} \cdot \left(\frac{V_{sig,rms}}{3 \cdot \sigma_{Vos}} \right)^2$$

- Refined result for flash ADC, assuming
 - Class-A, 1/2LSB matching with 3σ -confidence, 2^B components, additional E_{dyn} per clock cycle, partial supply usage (α)

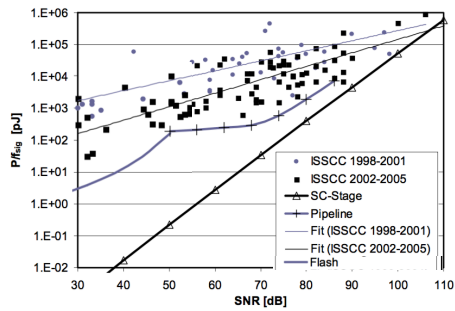
$$P = \left(12\pi \cdot \frac{1}{\alpha} \cdot C_{ox} \cdot A_T^2 \cdot 2^{3B} + 2 \cdot E_{dyn} \cdot 2^B \right) \cdot f_{sig}$$

- Example: $\alpha=2/3$, $C_{ox}=15\text{fF}/\mu\text{m}^2$, $A_T=3\text{mV} \cdot \mu\text{m}$, $E_{dyn}=60\text{fJ}$ (~ 10 gates in $0.13\mu\text{m}$ CMOS)

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Low SNR: Result



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Discussion

- Missing factors
 - Biasing, reference generator
 - S/H hold front-end
 - Cost of "high gain"
 - I/O power, digital power ... and more
- Shown results include only minor assumptions about technology
- Scaling brings some good, some bad news offsetting each other
 - CON: Lower V_{DD} , lower V_{swing}/V_{DD}
 - PRO: Lower I_{DD} , higher f_t enables moderate/weak inversion operation with high g_m/I_D
- Limit lines won't move much, unless someone hands us a new disruptive technology

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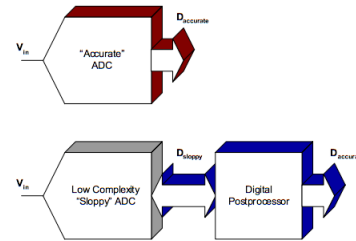
Future Opportunities

- More intelligent ADCs
 - Improved average power dissipation by adapting to instantaneous speed/resolution requirements
- "Sloppy" ADCs using significantly simpler circuits
 - Digital compensation of resulting non-idealities
 - Digital postprocessing is "free" at moderate to high SNR
- Digitally Assisted ADCs
 - How many analog transistors do we really need?

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Conventional vs. Digitally Assisted ADC



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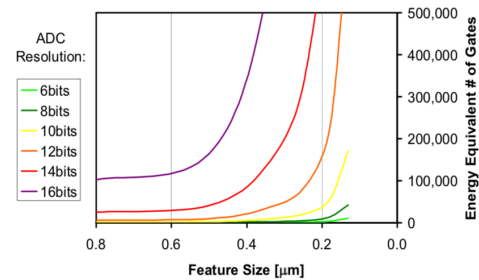
Digital Energy – Relative to ADC

- Example
 - Standard digital gate (NAND2) in 0.13 μm CMOS consumes about 6nW/Gate/MHz
 - Energy/Gate = 6fJ
 - State-of-the-art 10-bit Nyquist ADCs consume roughly 1mW/MSample/sec
 - Energy/Conversion = 1nJ
 - Energy equivalent number of gates (Assuming 10-bit ADC, 0.13 μm logic)
 - $1\text{nJ}/6\text{fJ} = 166,666$
- Up to several tens of thousand gates are "free" in terms of energy!

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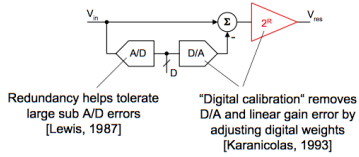
Digital Energy – Relative to ADC



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Example: Pipeline ADC

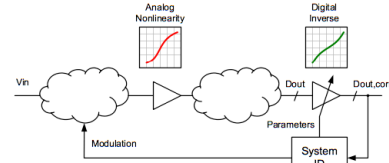


- Bottleneck: Fast, **highly linear** gain element
- 50-70% of total pipeline ADC power is consumed by interstage amplifiers

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Digitally Nonlinearity Compensation

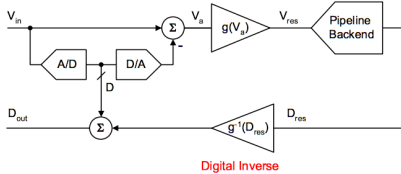


- Need system ID to determine optimum post distortion
- Possible to track variations over time without interrupting normal circuit operation

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Correction Concept

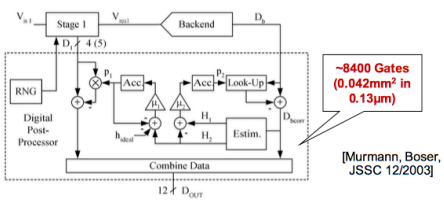


- V_{res} is digitized by pipeline backend
- Amplifier nonlinearity cancelled by digital inverse

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Prototype

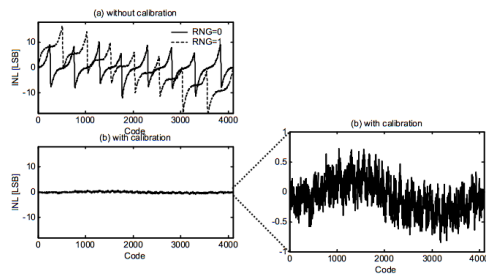


- Open-loop amplifier in first, most critical stage
- Statistics based system ID allows continuous parameter tracking
- Judicious analog/digital co-design

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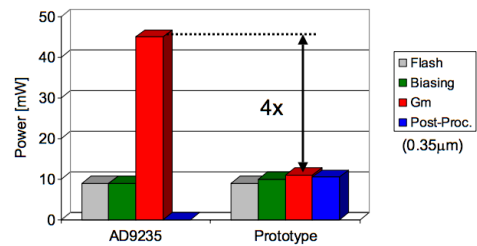
Measurement Results



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Stage1 Power Breakdown

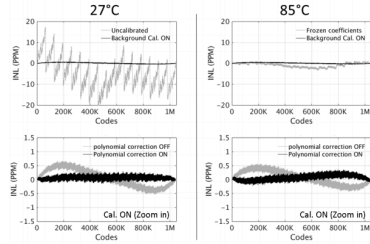


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14.7 Li, ISSCC 2018

- A Signal-Independent Background-Calibrating 20b 1MS/s SAR ADC with 0.3ppm INL

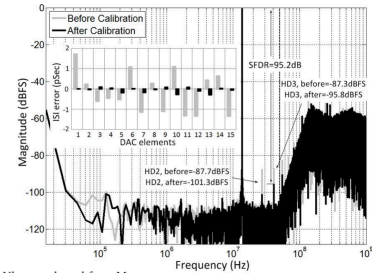


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14.1 He, ISSCC 2018

- A 50MHz-BW Continuous-Time $\Delta \Sigma$ ADC with Dynamic Error Correction Achieving 79.8dB SNDR and 95.2dB SFDR



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Future

- Today's ADCs are extremely well optimized
- For non-incremental improvements, we must explore new ideas in signal processing that tackle ADC inefficiency at the system level
 - Compressed sensing
 - Finite innovation rate sampling
 - Other ideas?

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Big Ideas

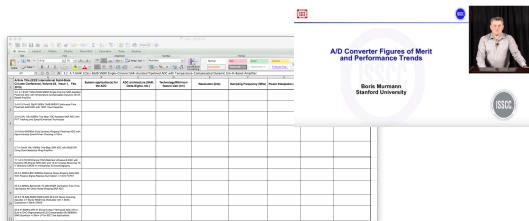
- FOM effective to compare performance of ADCs
- Performance trends and limits
 - Moving into digitally assisted designs

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Revisit: HW 1

- Read state-of-the-art ADC design publications (2019) and fill out EXCEL spec sheet
- Watch video of ADC performance trends (2014)



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Admin

- Proj 2 out

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